

VMMBZ16C1DD1 to VMMBZ33C1DD1

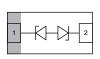
Vishay Semiconductors

RoHS

HALOGEN FREE

GREEN

Single-Line Bidirectional ESD-Protection Diode in DFN1006-2B





MARKING (example only)



Bar = pin 1 marking X = date code YY = type code (see table below)

LINKS TO ADDITIONAL RESOURCES







FEATURES

- Compact DFN1006-2B package
- Low package height < 0.5 mm
- 1-line bidirectional ESD-protection
- AEC-Q101 qualified available
- Working range ±14 V; ± 28 V
- ESD immunity acc. IEC 61000-4-2 ±15 kV to ±30 kV contact discharge ±15 kV to ±30 kV air discharge
- Lead plating: Sn (e3)
- Soldering can be checked by standard vision inspection
- AOI = Automated Optical Inspection
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Soldering Recommendations for DFN Packages:

please see Application Note: www.vishay.com/doc?86198

SPICE	A
Models	Application

ORDERING INFORMATION						
	ENVIRONMENTAL AND QUALITY CODE					
PART NUMBER (EXAMPLE)	AEC-Q101 QUALIFIED	RoHS COMPLIANT + LEAD (Pb)-FREE TERMINATIONS	TIN PLATED	10K PER 7" REEL (8 mm TAPE)	ORDERING CODE (EXAMPLE)	
		GREEN		MOQ = 10K/BOX		
VMMBZ16C1DD1	-	G	3	-08	VMMBZ16C1DD1-G3-08	
VMMBZ16C1DD1	Н	G	3	-08	VMMBZ16C1DD1HG3-08	

PACKAGE DATA								
DEVICE NAME	PACKAGE NAME	TYPE CODE	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS		
VMMBZ16C1DD1	DFN1006-2B	2Y	0.83 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C		
VMMBZ33C1DD1	DFN1006-2B	2N	0.83 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C		

VMMBZ16C1DD1 to VMMBZ33C1DD1

Vishay Semiconductors

ABSOLUTE MAXIMUM RATINGS VMMBZ16C1DD1 (T _{amb} = 25 °C, unless otherwise specified)							
PARAMETER TEST CONDITIONS SYMBOL VALUE UNI							
Peak pulse current	Acc. IEC 61000-4-5, 8/20 μs/single shot	I _{PPM}	4	Α			
Peak pulse power	Acc. IEC 61000-4-5, 8/20 μs/single shot ⁽¹⁾	P _{PP}	108	W			
Peak pulse current	$t_p = 10/1000 \ \mu s^{(1)}$	I _{PPM}	0.65	Α			
Peak pulse power	t _p = 10/1000 μs ⁽¹⁾	P_{PP}	15	W			
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses (1)	V	30	kV			
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses (1)	V_{ESD}	30	kV			
Operating temperature	Junction temperature	T_J	-55 to +150	°C			
Storage temperature		T _{stg}	-55 to +150	°C			

ABSOLUTE MAXIMUM RATINGS VMMBZ33C1DD1 (T _{amb} = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT			
Peak pulse current	Acc. IEC 61000-4-5, 8/20 μs/single shot	I _{PPM}	1.7	Α			
Peak pulse power	Acc. IEC 61000-4-5, 8/20 μs/single shot ⁽¹⁾	P _{PP}	100	W			
Peak pulse current	t _p = 10/1000 μs ⁽¹⁾	I _{PPM}	0.3	Α			
Peak pulse power	$t_p = 10/1000 \ \mu s^{(1)}$	P _{PP}	15	W			
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses (1)	V	15	kV			
E3D Illillullity	Air discharge acc. IEC 61000-4-2; 10 pulses (1)	V_{ESD}	15	kV			
Operating temperature	Junction temperature	TJ	-55 to +150	°C			
Storage temperature		T _{stg}	-55 to +150	°C			

ELECTRICAL CHARAC (T _{amb} = 25 °C, unless oth	CTERISTICS VMMBZ16C1DD1 nerwise specified)					
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	14	V
Reverse voltage	At I _R = 0.1 μA	V _R	14	-	-	V
Reverse current	At V _R = 14 V	I _R	-	< 1	10	nA
	At $V_R = 14 \text{ V}$; $T_J = 150 ^{\circ}\text{C}^{(1)}$		-	0.06	10	μA
Develope by a clade way well a co	At I _R = 1 mA		16.2	16.7	17.3	V
Reverse breakdown voltage	At $I_R = 1$ mA; $T_J = -40$ °C to $+150$ °C $^{(1)}$	V_{BR}	15	-	18.7	V
Reverse clamping voltage	At $I_{PP} = I_{PPM} = 4 \text{ A}$, $t_p = 8/20 \mu\text{s}$	V _C	20	23.7	27	V
	$t_p = 100 \text{ ns (TLP)}; I_{TLP} = 16 \text{ A}^{(1)}$	V _{C_TLP}	-	26	-	V
Dynamic resistance	$t_p = 100 \text{ ns (TLP)}^{(1)}$	r _{dyn}	-	0.55	-	Ω
Capacitance	At $V_R = 0 V$; $f = 1 MHz$	C _D	12	14.5	17	pF

ELECTRICAL CHARACTERISTICS VMMBZ33C1DD1 (T _{amb} = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines	
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	28	V	
Reverse voltage	At I _R = 0.1 μA	V _R	28	-	-	V	
D	At V _R = 28 V	I _R	-	< 1	10	nA	
Reverse current	At $V_R = 28 \text{ V}$; $T_J = 150 ^{\circ}\text{C}^{(1)}$		-	0.1	10	μA	
De constituent de constituent	At I _R = 1 mA	V _{BR}	32.7	33.7	34.8	V	
Reverse breakdown voltage	At $I_R = 1$ mA; $T_J = -40$ °C to $+150$ °C $^{(1)}$		30	-	39.7	V	
Deverse elemning veltage	At $I_{PP} = I_{PPM} = 1.7 \text{ A}$, $t_p = 8/20 \mu\text{s}$	V _C	40	49	59	V	
Reverse clamping voltage	$t_p = 100 \text{ ns (TLP)}; I_{TLP} = 16 \text{ A}^{(1)}$	V _{C_TLP}	-	88	-	V	
Dynamic resistance	t _p = 100 ns (TLP) ⁽¹⁾	r _{dyn}	-	3.3	-	Ω	
Capacitance	At $V_R = 0 V$; $f = 1 MHz$	C_D	6	8	10	pF	

Note

⁽¹⁾ Guaranteed by design. Tested during device characterization

Vishay Semiconductors

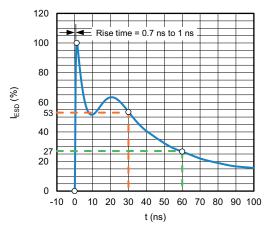


Fig. 1 - ESD Discharge Current Wave Form Acc. IEC 61000-4-2 (330 Ω / 150 pF)

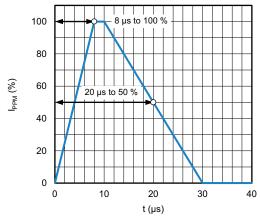


Fig. 2 - 8/20 µs Peak Pulse Current Wave Form Acc. IEC 61000-4-5

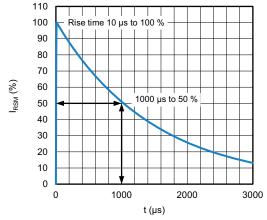


Fig. 3 - 10/1000 µs Peak Pulse Current Wave Form

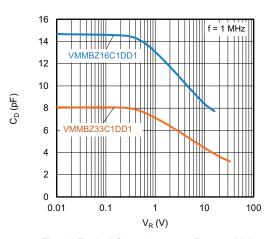


Fig. 4 - Typical Capacitance vs. Reverse Voltage

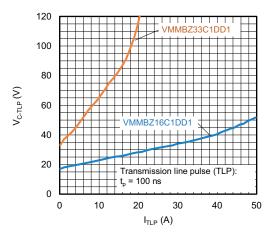


Fig. 5 - Typical Clamping Voltage vs. Peak Pulse Current

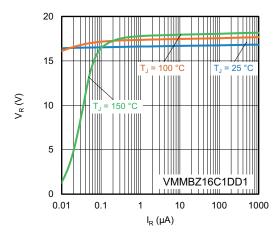


Fig. 6 - Typical Reverse Voltage vs. Reverse Current

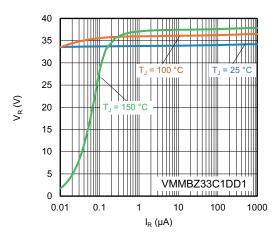


Fig. 7 - Typical Reverse Voltage vs. Reverse Current

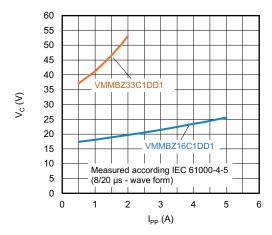


Fig. 8 - Typical Peak Clamping Voltage vs. Peak Pulse Current

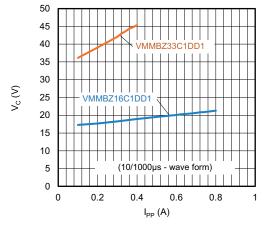


Fig. 9 - Typical Peak Clamping Voltage vs. Peak Pulse Current

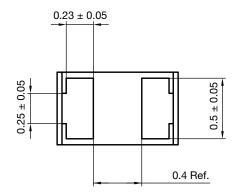




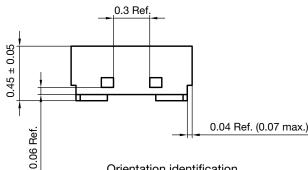
www.vishay.com

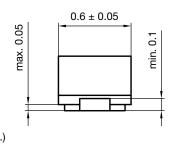
Vishay Semiconductors

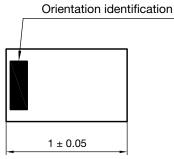
PACKAGE DIMENSIONS in millimeters (inches): DFN1006-2B



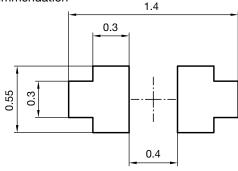
Package = Chip Dimension in mm









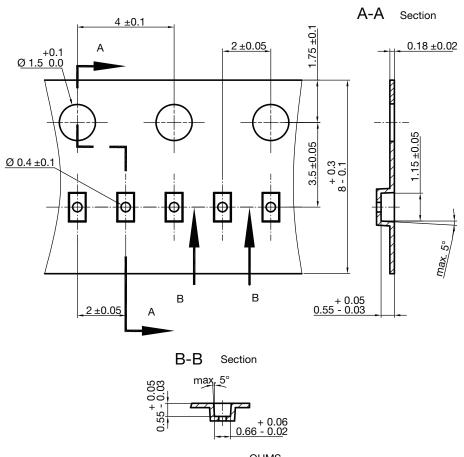


Document no.: S8-V-3906.04-059 (4) Created - Date: 11-Jul-2018 Rev.5 - Date: 17-Sep-2021

23191

Vishay Semiconductors

CARRIER TAPE DFN1006-2B



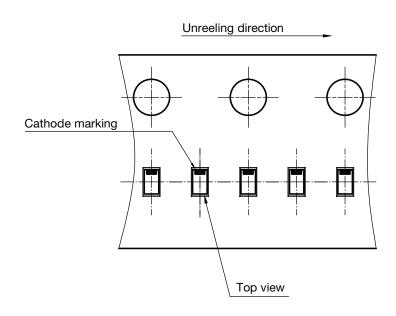
S8-V-3906.04-063 (4) created 28.10.2019

S8-V-3906.04-064 (4)

created 28.10.2019

surface resistance: 10^5 - $10^{11} \frac{OHMS}{SQ}$ Cummulative tolerances of 10 sprocket holes is \pm 0.2 mm

ORIENTATION IN CARRIER TAPE DFN1006-2B



Rev. 1.0, 19-Jan-2022 6 Document Number: 86193



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Vishay:

<u>VMMBZ16C1DD1-G3-08</u> <u>VMMBZ16C1DD1HG3-08</u> <u>VMMBZ33C1DD1-G3-08</u> <u>VMMBZ33C1DD1HG3-08</u> VMMBZ23C1DD1-G3-08 VMMBZ23C1DD1HG3-08